Product data sheet

1. General description

Ultrafast, dual common cathode, epitaxial rectifier diodes in a TO252 (DPAK) plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- · Soft recovery characteristic
- · Low forward voltage drop
- Reverse surge capability
- · High thermal cycling performance

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			200			V
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 119$ °C; both diodes conducting; Fig. 5; Fig. 6		10		А	
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 119 °C; square-wave pulse; per diode		10		А	
I_{FSM}	non-repetitive peak	t_p = 10 ms; sine-wave pulse; per diode		50			Α
	forward current	t _p = 8.3 ms; sine-wave pulse; per diode	55			Α	
Symbol	Parameter	Conditions	Min Typ Max		Unit		
Static ch	aracteristics						
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 2</u>		-	0.95	1.1	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 2</u>		-	8.0	0.895	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 2</u>		-	1.1	1.25	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	ramp recovery; $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 3		-	15	25	ns
		step recovery; when switched from $I_F = 0.5 \text{ A to } I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$		-	10	20	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode [1]		
3	A2	anode 2		A1
mb	К	mounting base; connected to cathode		K sym125

^[1] It is not possible to connect to pin 2 of the TO252 package.

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYQ28ED-200	TO252	BYQ28ED-200, 118	Reel	2500	TO252N	14-Nov-2016

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYQ28ED-200	Q28E20

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		200	V
V_{RWM}	crest working reverse voltage		200	V
V_R	reverse voltage	δ = 1.0; square-wave pulse;	200	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 119 °C; both diodes conducting; <u>Fig. 6</u> ; <u>Fig. 7</u>	10	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 119 °C$; square-wave pulse; per diode	10	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; sine-wave pulse; per diode; Fig. 3	50	Α
	forward current	t_p = 8.3 ms; sine-wave pulse; per diode	55	Α
I _{RM}	peak reverse recovery current	$\delta = 0.001$; $t_p = 2 \mu s$	0.2	Α
I _{RSM}	non-repetitive peak reverse current	$t_p = 100 \ \mu s$	0.2	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C
Electrostat	tic discharge			
V _{ESD}	electrostatic discharge voltage	all pins; human body model; C = 250 pF; R = 1.5 kΩ	8	kV

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	3	K/W
	mounting base	with heatsink compound; per diode; Fig 1	-	-	4.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

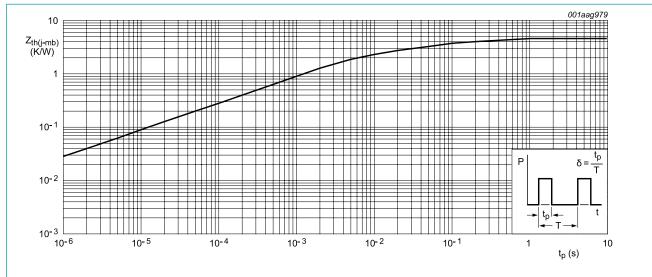
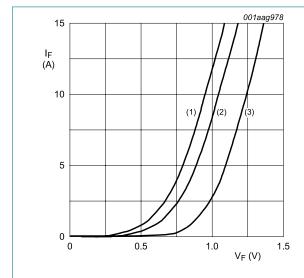


Fig. 1. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V_{F}	forward voltage	I _F = 5 A; T _j = 150 °C; <u>Fig. 2</u>	-	0.8	0.895	V
		I _F = 5 A; T _j = 25 °C; <u>Fig. 2</u>	-	0.95	1.1	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 2</u>	-	1.1	1.25	V
I_R	reverse current	V _R = 200 V; T _j = 25 °C	-	2	10	μA
		V _R = 200 V; T _j = 100 °C	-	0.1	0.2	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 4	-	4	9	nC
t _{rr}	reverse recovery time	ramp recovery; $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 4	-	15	25	ns
		step recovery; when switched from $I_F = 0.5 \text{ A to } I_R = 1 \text{ A}$; measured at $I_R = 0.25 \text{ A}$	-	10	20	ns
I _{RM}	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$	-	0.5	0.7	А
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A; } dI_F/dt = 10 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } Fig. 5$	-	1	-	V



(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_i = 25 °C; maximum values



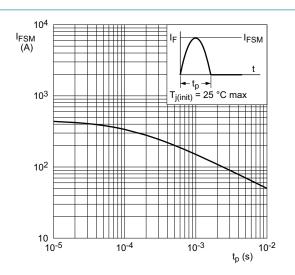
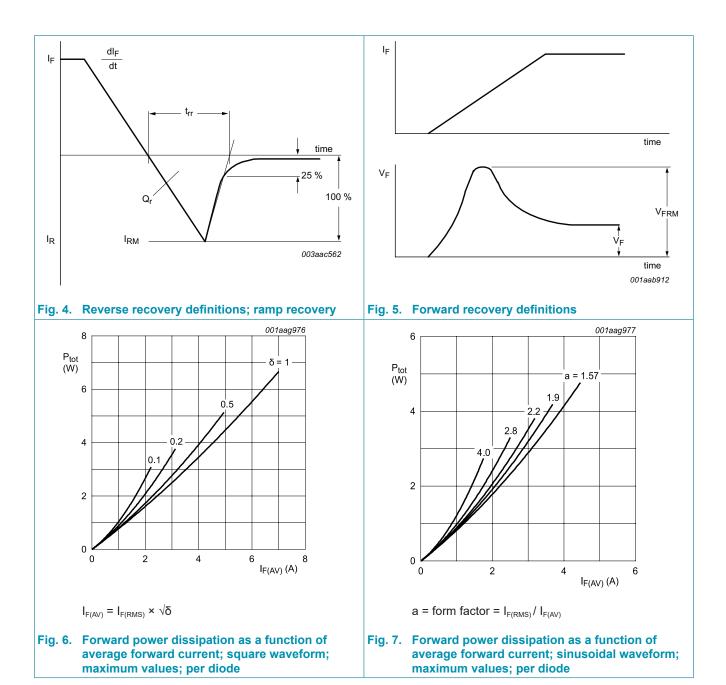
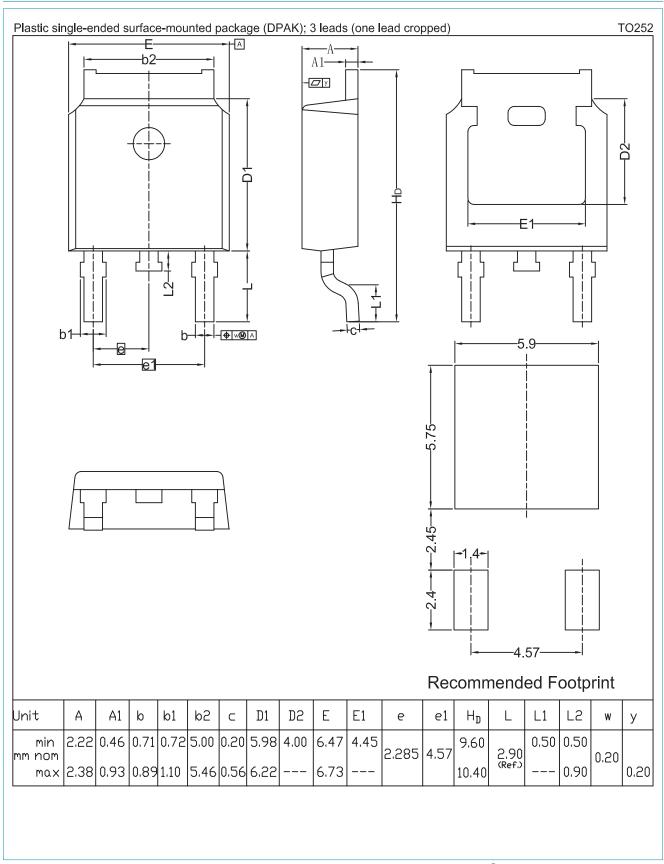


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values



11. Package outline



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12. Revision history

Table 8. Revision history

Tuble 0. Itevision mistor	J							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
BYQ28ED-200 v.7	20190923	Product data sheet	-	BYQ28ED-200 v.6				
Modifications: • Update Marking code. • Update ordering information.								
BYQ28ED-200 v.6	20181218	Product data sheet	-	BYQ28ED-200 v.5				
Modifications: Ad	d IFSM figure.							
BYQ28ED-200 v.5	20180224	Product data sheet	-	BYQ28_SER_E_ED_4				
Modifications: Ch	ange from NXP version to We	eEn version						
BYQ28_SER_E_ED_4	20071205	Product data sheet	-	BYQ28E_SERIES_3				
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Limiting values table: some parameter descriptions amended to conform to latest standards; IFRM conditions amended; VESD row added. Characteristics: Qrr changed to Qr 'recovered charge'; trr1 and trr2 changed to trr with 'ramp recovery' and 'step recovery' added to conditions. 							
BYQ28E_SERIES_3	19981001	Product specification	-	BYQ28E_SERIES_2				
BYQ28E_SERIES_2	19980701	Product specification	-	BYQ28E_SERIES_1; BYQ28EB_SERIES_1				
BYQ28E_SERIES_1; BYQ28EB_SERIES_1	19960801	Product specification	-	-				

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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